12V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	I_D max T_A = +25°C
-12V	14.8mΩ @ V_{GS} = -4.5V	-9.5A
	19mΩ @ V_{GS} = -2.5V	-8.5A
	26mΩ @ V_{GS} = -1.8V	-7.2A
	32mΩ @ V_{GS} = -1.5V	-6.6A

Features

- 0.6mm profile – ideal for low profile applications
- PCB footprint of 4mm^2
- Low Gate Threshold Voltage
- Fast Switching Speed
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

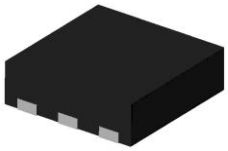
Description

This MOSFET is designed specifically for use in battery management applications.

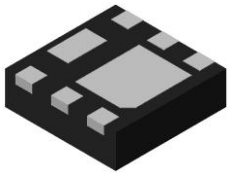
Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e4
- Weight: 0.0065 grams (Approximate)

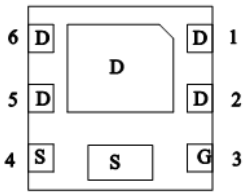
U-DFN2020-6



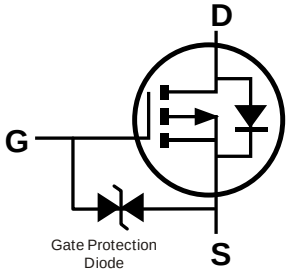
Top View



Bottom View



Pin Out
Bottom View



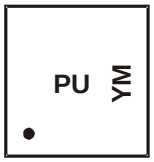
Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP1022UFDF-7	U-DFN2020-6	3,000/Tape & Reel
DMP1022UFDF-13	U-DFN2020-6	10,000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



PU = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: A = 2013)
M = Month (ex: 9 = September)

Date Code Key

Year	2013	2014	2015	2016	2017	2018	2019	2020	2021	2022
Code	A	B	C	D	E	F	G	H	I	J

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	-12	V
Gate-Source Voltage			V_{GSS}	±8	V
Continuous Drain Current (Note 6) V_{GS} = -4.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	-9.5 -7.6	A
	t<5s	T_A = +25°C T_A = +70°C	I_D	-11.0 -8.8	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I_{DM}	-90	A
Continuous Source-Drain Diode Current		T_A = +25°C T_C = +25°C	I_S	-2.5 -7.1	A
Pulsed Source-Drain Diode Current (10µs pulse, duty cycle = 1%)			I_{SM}	-50	A

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	0.73	W
	T_A = +70°C		0.47	
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	$R_{\theta JA}$	172	°C/W
	t<5s		128	
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	2.1	W
	T_A = +70°C		1.3	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	$R_{\theta JA}$	59	°C/W
	t<5s		45	
Thermal Resistance, Junction to Case (Note 6)	Steady state	$R_{\theta JC}$	5.1	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-12	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	—	—	-200	nA	V_{DS} = -12V, V_{GS} = 0V
Zero Gate Voltage Drain Current T_J = +55°C (Note 8)	I_{DSS}	—	—	-2	µA	V_{DS} = -12V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±10	µA	V_{GS} = ±8V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	-0.35	—	-0.8	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	12	14.8	mΩ	V_{GS} = -4.5V, I_D = -4A
			15	19		V_{GS} = -2.5V, I_D = -4A
			20	26		V_{GS} = -1.8V, I_D = -4A
			23	32		V_{GS} = -1.5V, I_D = -2A
Diode Forward Voltage	V_{SD}	—	-0.8	-1.2	V	V_{GS} = 0V, I_S = -8A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	2,712	—	pF	V_{DS} = -10V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	514	—		
Reverse Transfer Capacitance	C_{rss}	—	467	—		
Gate Resistance	R_g	—	8.6	18	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge	Q_g	—	48.3	—	nC	V_{GS} = -8V, V_{DS} = -6V, I_D = -10A
Total Gate Charge	Q_g	—	28.6	—		V_{GS} = -4.5V, V_{DS} = -6V, I_D = -10A
Gate-Source Charge	Q_{gs}	—	4.2	—		
Gate-Drain Charge	Q_{gd}	—	7.0	—		
Turn-On Delay Time	$t_{D(on)}$	—	25.1	—	ns	V_{DS} = -6V, V_{GS} = -4.5V, R_G = 1Ω, I_D = -8A
Turn-On Rise Time	t_r	—	39.8	—		
Turn-Off Delay Time	$t_{D(off)}$	—	141	—		
Turn-Off Fall Time	t_f	—	147	—		

Notes:
5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

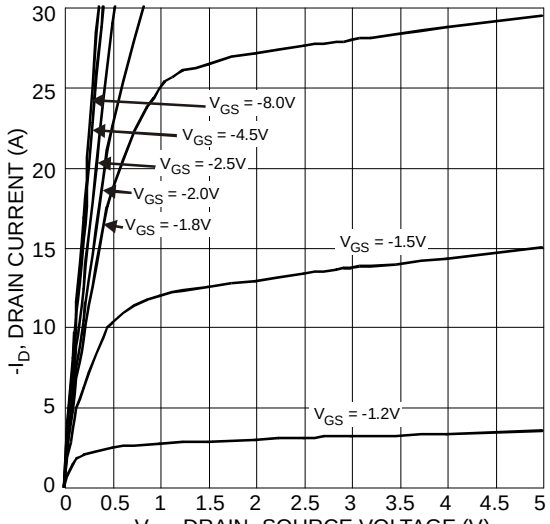


Figure 1 Typical Output Characteristics

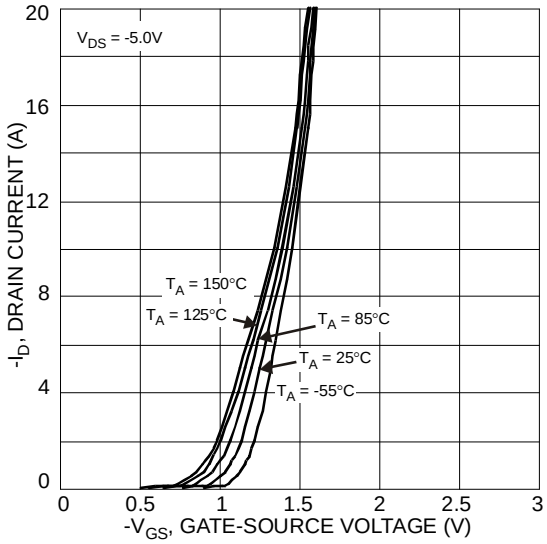


Figure 2 Typical Transfer Characteristics

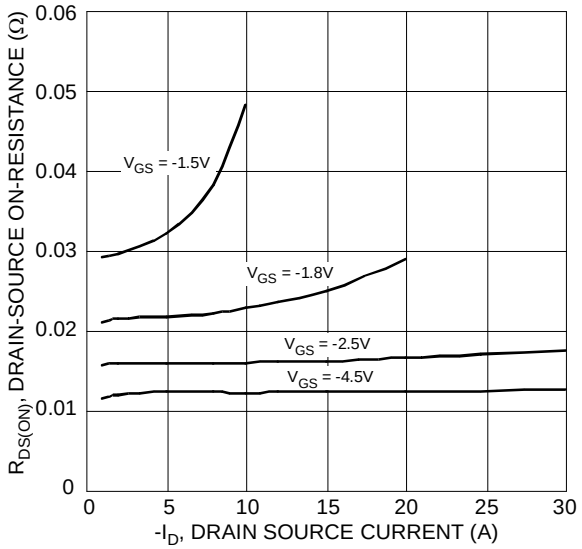


Figure 3 Typical On-Resistance vs.
Drain Current and Gate Voltage

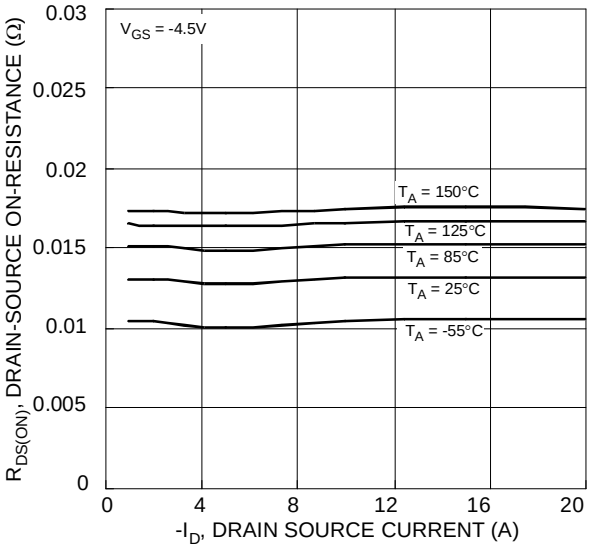


Figure 4 Typical On-Resistance vs.
Drain Current and Temperature

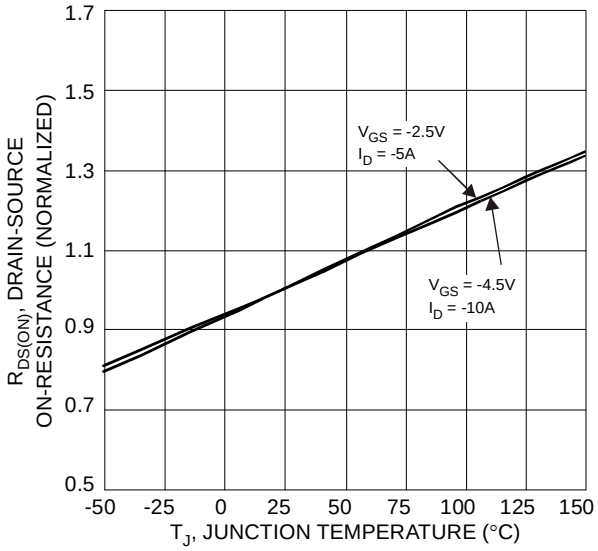


Figure 5 On-Resistance Variation with Temperature

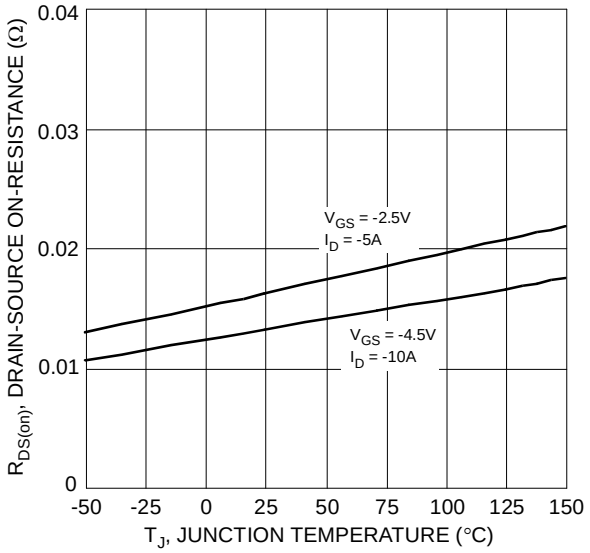


Figure 6 On-Resistance Variation with Temperature

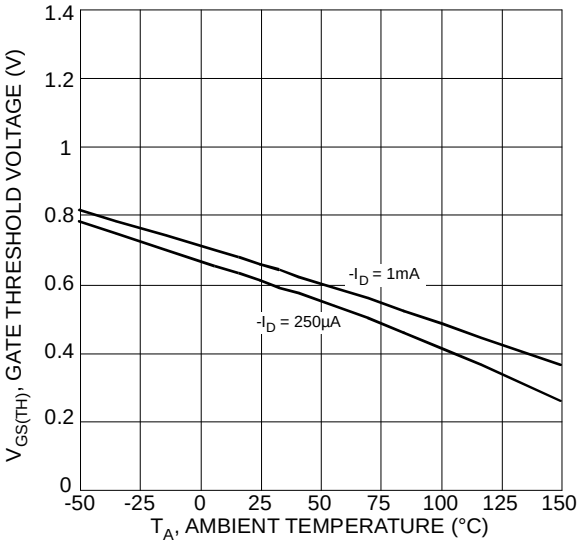


Figure 7 Gate Threshold Variation vs. Ambient Temperature

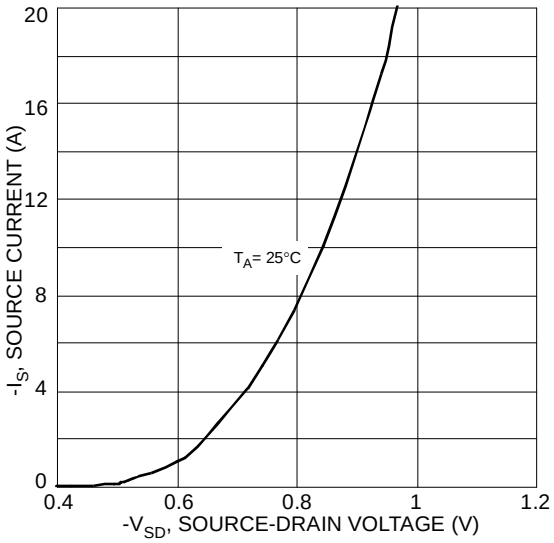


Figure 8 Diode Forward Voltage vs. Current

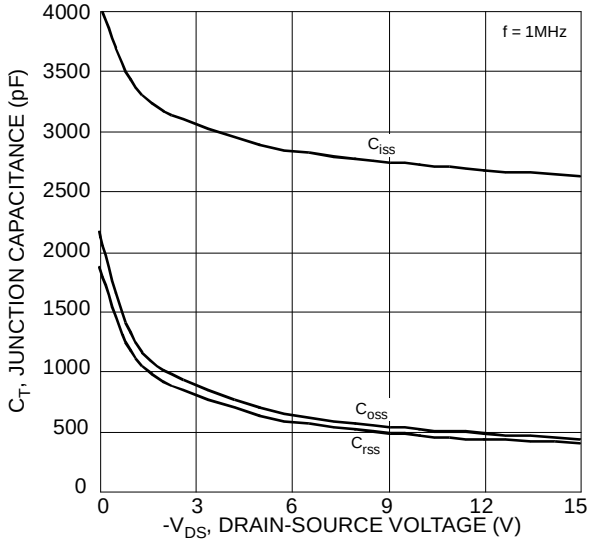


Figure 9 Typical Junction Capacitance

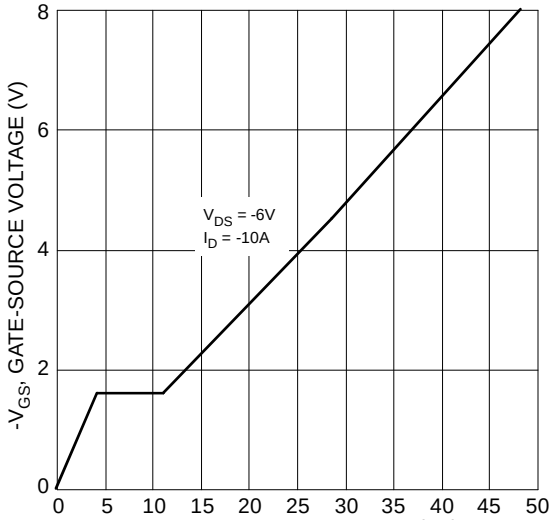


Figure 10 Gate-Charge Characteristics

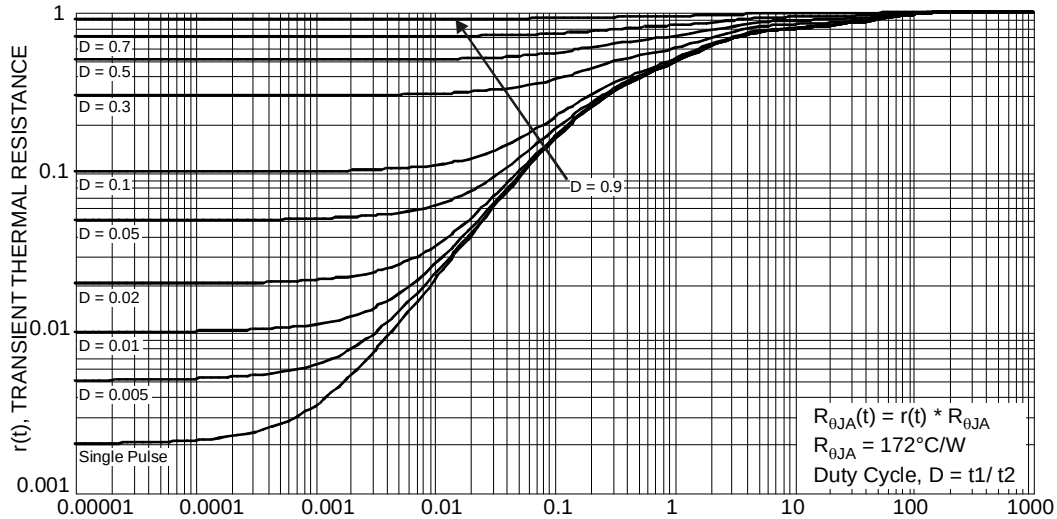
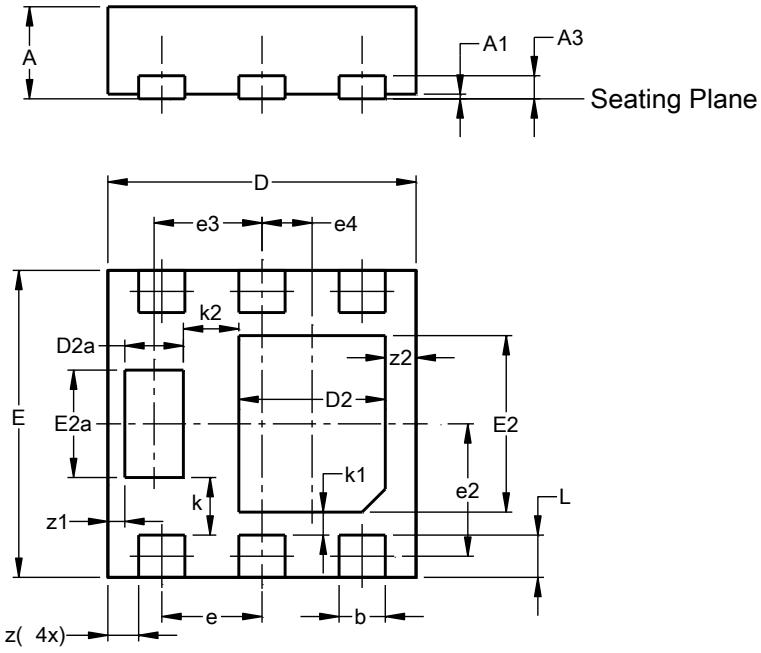


Figure 11 Transient Thermal Resistance

Package Outline Dimensions

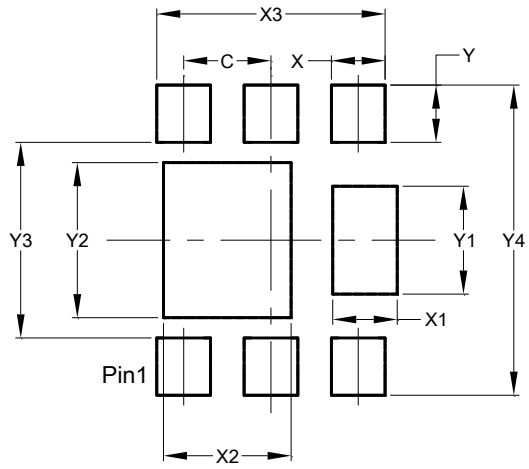
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



U-DFN2020-6 (Type F)			
Dim	**Min**	**Max**	**Typ**
A	0.57	0.63	0.60
A1	0.00	0.05	0.03
A3	-	-	0.15
b	0.25	0.35	0.30
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
D2a	0.33	0.43	0.38
E	1.95	2.05	2.00
E2	1.05	1.25	1.15
E2a	0.65	0.75	0.70
e	0.65 BSC		
e2	0.863 BSC		
e3	0.70 BSC		
e4	0.325 BSC		
k	0.37 BSC		
k1	0.15 BSC		
k2	0.36 BSC		
L	0.225	0.325	0.275
z	0.20 BSC		
z1	0.110 BSC		
z2	0.20 BSC		
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
C	0.650
X	0.400
X1	0.480
X2	0.950
X3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300

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